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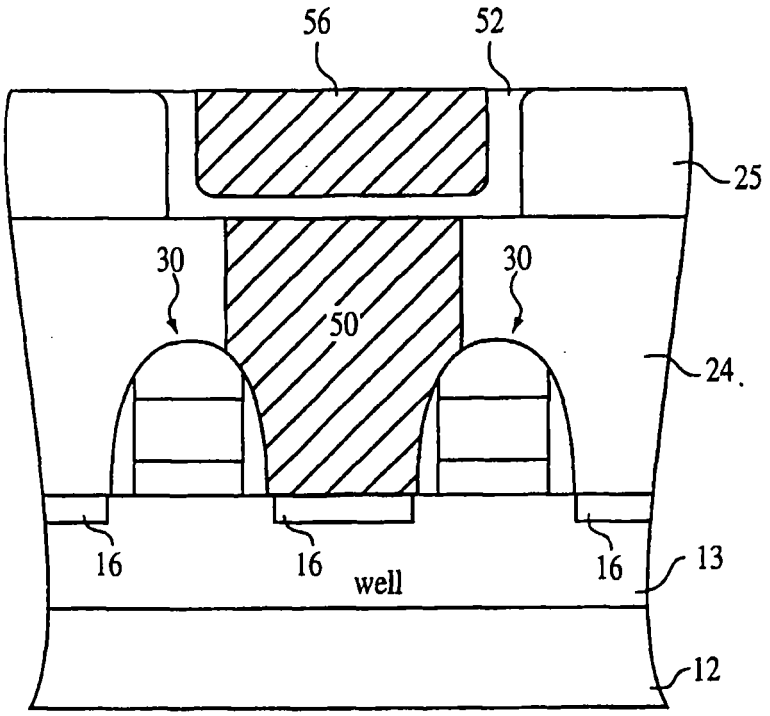
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(54) Title: USE OF AIN AS COPPER PASSIVATION LAYER AND THERMAL CONDUCTOR



(57) Abstract: A copper interconnect structure is disclosed as comprising a copper layer and an aluminum nitride layer formed over the copper layer. The aluminum nitride layer passivates the copper layer surface and enhances the thermal conductivity of a semiconductor substrate by radiating heat from the substrate as well as from the copper layer.

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